

NTLUS3A18PZ

MOSFET – Power, Single, P-Channel, UDFN, 2.0x2.0x0.55 mm -20 V, -8.2 A



ON Semiconductor®

www.onsemi.com

Features

- UDFN Package with Exposed Drain Pads for Excellent Thermal Conduction
- Low Profile UDFN 2.0x2.0x0.55 mm for Board Space Saving
- Ultra Low $R_{DS(on)}$
- ESD Diode–Protected Gate
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Optimized for Power Management Applications for Portable Products, such as Cell Phones, Media Tablets, PMP, DSC, GPS, and Others
- Battery Switch
- High Side Load Switch

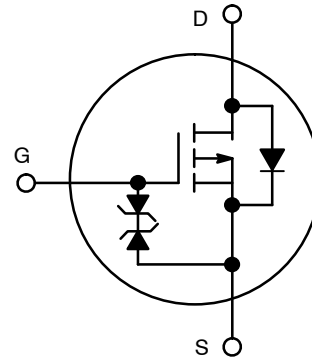
MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter		Symbol	Value	Unit	
Drain-to-Source Voltage		V_{DSS}	-20	V	
Gate-to-Source Voltage		V_{GS}	± 8.0	V	
Continuous Drain Current (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	I_D	-8.2	A
				$T_A = 85^\circ\text{C}$	
Continuous Drain Current (Note 1)	$t \leq 5 \text{ s}$	$T_A = 25^\circ\text{C}$	I_D	-12.2	A
Power Dissipation (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	P_D	1.7	W
				$t \leq 5 \text{ s}$	
Continuous Drain Current (Note 2)	Steady State	$T_A = 25^\circ\text{C}$	I_D	-5.1	A
		$T_A = 85^\circ\text{C}$		-3.7	
Power Dissipation (Note 2)		$T_A = 25^\circ\text{C}$	P_D	0.7	W
Pulsed Drain Current		$t_p = 10 \mu\text{s}$	I_{DM}	-25	A
Operating Junction and Storage Temperature		T_J, T_{STG}	-55 to 150	$^\circ\text{C}$	
ESD (HBM, JESD22-A114)		V_{ESD}	2000	V	
Source Current (Body Diode) (Note 2)		I_S	-1.7	A	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		T_L	260	$^\circ\text{C}$	

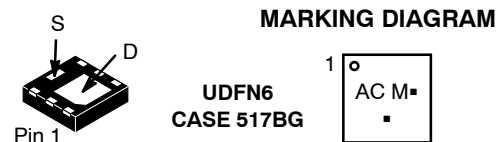
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Surface Mounted on FR4 Board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).
2. Surface-mounted on FR4 board using the minimum recommended pad size of 30 mm², 2 oz. Cu.

MOSFET		
$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D MAX
-20 V	18 m Ω @ -4.5 V	-8.2 A
	25 m Ω @ -2.5 V	
	50 m Ω @ -1.8 V	
	90 m Ω @ -1.5 V	

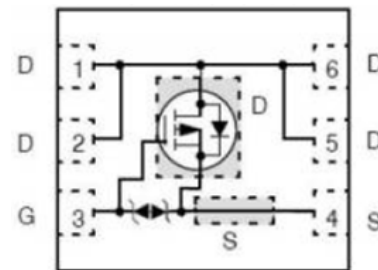


P-Channel MOSFET



AC = Specific Device Code
M = Date Code
▪ = Pb-Free Package
(Note: Microdot may be in either location)

PIN CONNECTIONS



(Top View)

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

NTLUS3A18PZ

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient – Steady State (Note 3)	$R_{\theta JA}$	72	°C/W
Junction-to-Ambient – $t \leq 5$ s (Note 3)	$R_{\theta JA}$	33	
Junction-to-Ambient – Steady State min Pad (Note 4)	$R_{\theta JA}$	189	

3. Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).

4. Surface-mounted on FR4 board using the minimum recommended pad size of 30 mm², 2 oz. Cu.

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
-----------	--------	----------------	-----	-----	-----	-------

OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0$ V, $I_D = -250$ μ A	-20			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = -250$ μ A, ref to 25°C		+10		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0$ V, $V_{DS} = -20$ V			-1.0	μ A
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0$ V, $V_{GS} = \pm 5.0$ V			± 5	μ A

ON CHARACTERISTICS (Note 5)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}$, $I_D = -250$ μ A	-0.4		-1.0	V
Negative Threshold Temp. Coefficient	$V_{GS(TH)}/T_J$			3.0		mV/°C
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = -4.5$ V, $I_D = -7.0$ A		14.6	18	m Ω
		$V_{GS} = -2.5$ V, $I_D = -5.0$ A		19	25	
		$V_{GS} = -1.8$ V, $I_D = -3.0$ A		25	50	
		$V_{GS} = -1.5$ V, $I_D = -1.0$ A		40	90	
Forward Transconductance	g_{FS}	$V_{DS} = -5$ V, $I_D = -3.0$ A		40		S

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C_{ISS}	$V_{GS} = 0$ V, $f = 1$ MHz, $V_{DS} = -15$ V		2240		pF
Output Capacitance	C_{OSS}			240		
Reverse Transfer Capacitance	C_{RSS}			210		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = -4.5$ V, $V_{DS} = -15$ V; $I_D = -4.0$ A		28		nC
Threshold Gate Charge	$Q_{G(TH)}$			1.0		
Gate-to-Source Charge	Q_{GS}			2.9		
Gate-to-Drain Charge	Q_{GD}			8.8		

SWITCHING CHARACTERISTICS, $V_{GS} = 4.5$ V (Note 6)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = -4.5$ V, $V_{DD} = -15$ V, $I_D = -4.0$ A, $R_G = 1$ Ω		8.6		ns
Rise Time	t_r			15		
Turn-Off Delay Time	$t_{d(OFF)}$			150		
Fall Time	t_f			88		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0$ V, $I_S = -1.0$ A	$T_J = 25^\circ\text{C}$	0.63	1.0	V
			$T_J = 125^\circ\text{C}$	0.50		
Reverse Recovery Time	t_{RR}	$V_{GS} = 0$ V, $dI_S/dt = 100$ A/ μ s, $I_S = -1.0$ A		26.1		ns
Charge Time	t_a			10.2		
Discharge Time	t_b			15.9		
Reverse Recovery Charge	Q_{RR}			12		nC

5. Pulse Test: pulse width ≤ 300 μ s, duty cycle $\leq 2\%$.

6. Switching characteristics are independent of operating junction temperatures.

NTLUS3A18PZ

TYPICAL CHARACTERISTICS

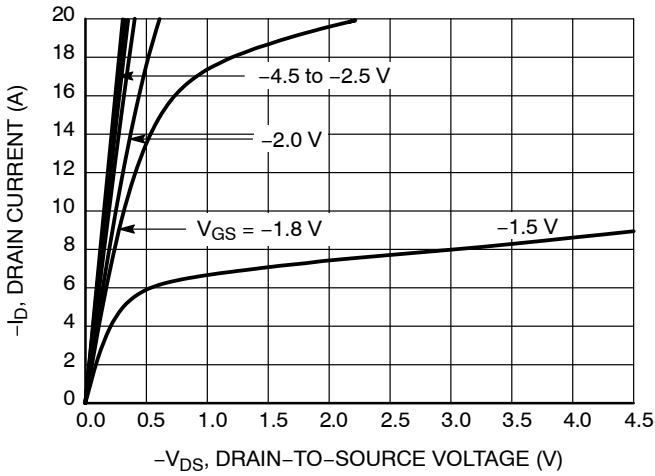


Figure 1. On-Region Characteristics

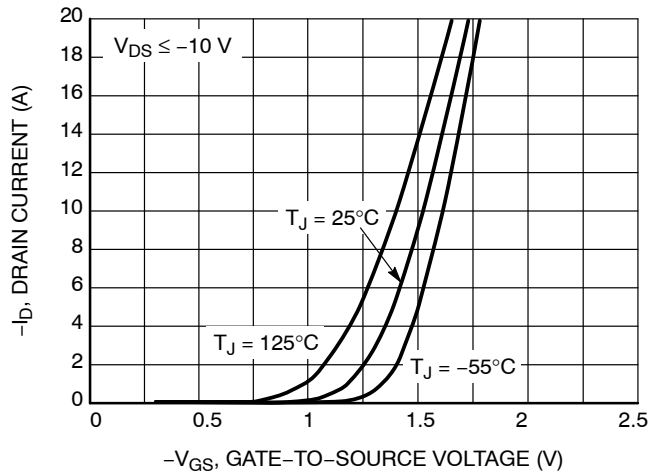


Figure 2. Transfer Characteristics

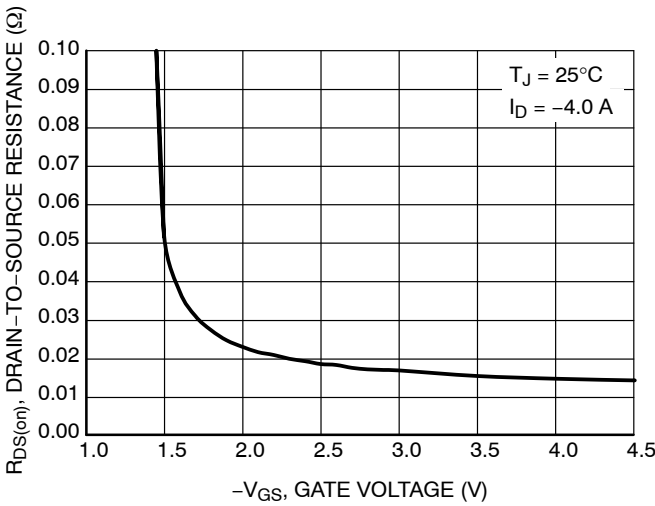


Figure 3. On-Resistance vs. Gate-to-Source Voltage

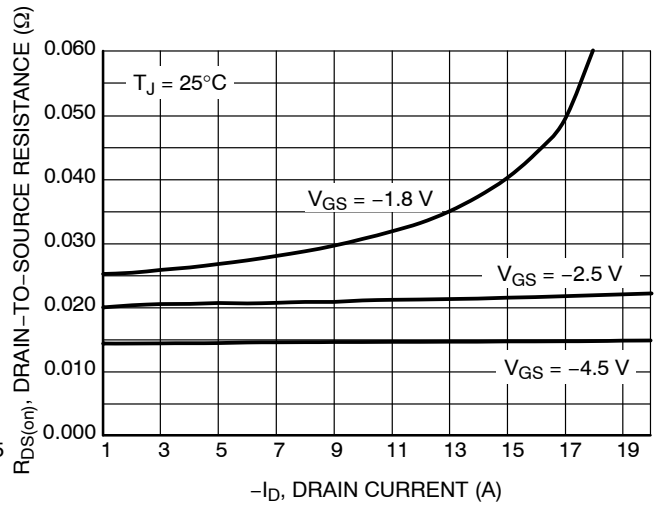


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

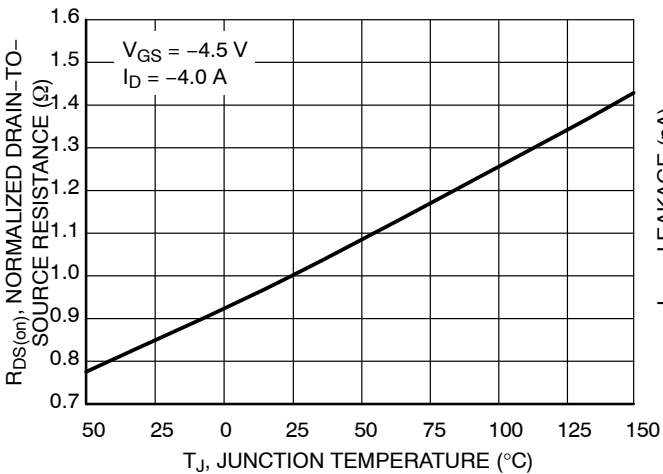


Figure 5. On-Resistance Variation with Temperature

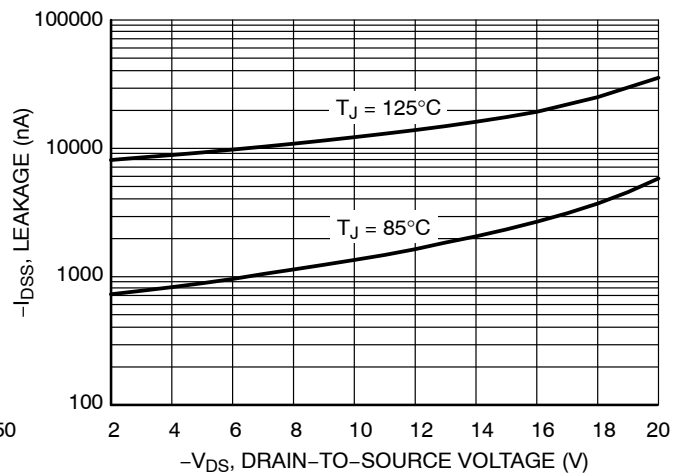


Figure 6. Drain-to-Source Leakage Current vs. Voltage

NTLUS3A18PZ

TYPICAL CHARACTERISTICS

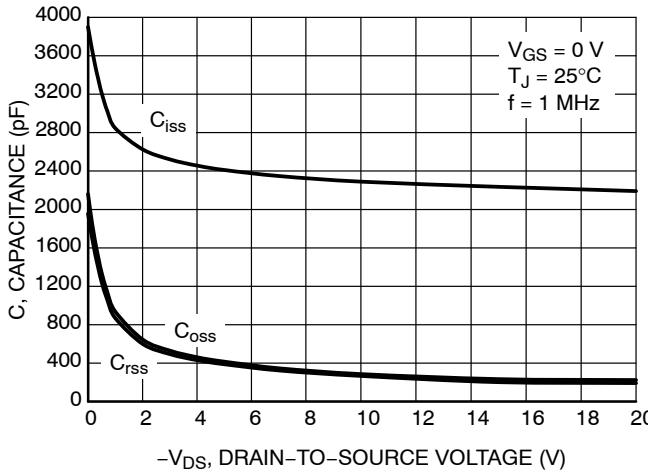


Figure 7. Capacitance Variation

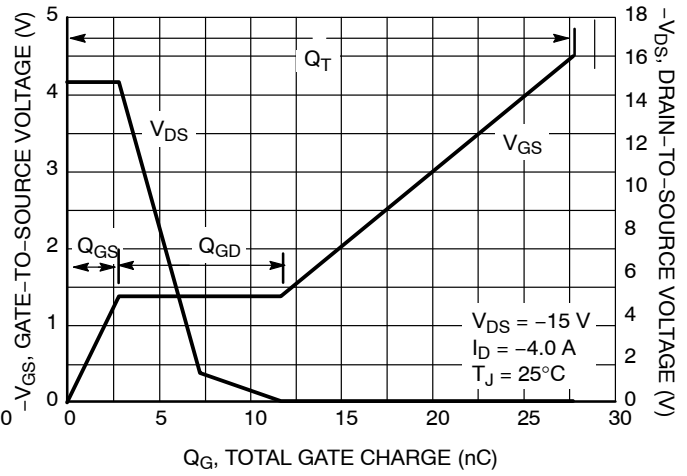


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

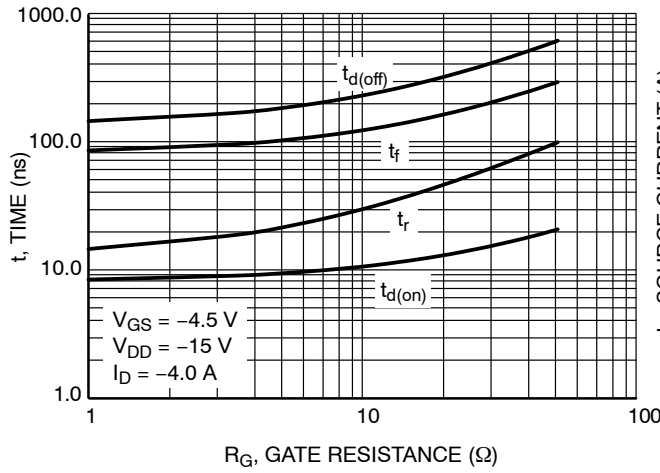


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

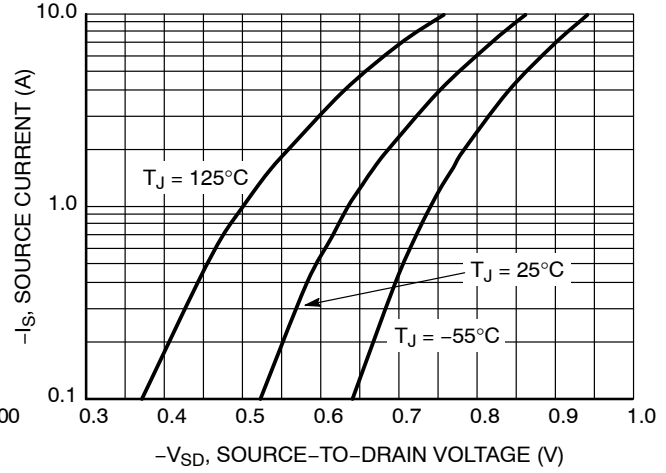


Figure 10. Diode Forward Voltage vs. Current

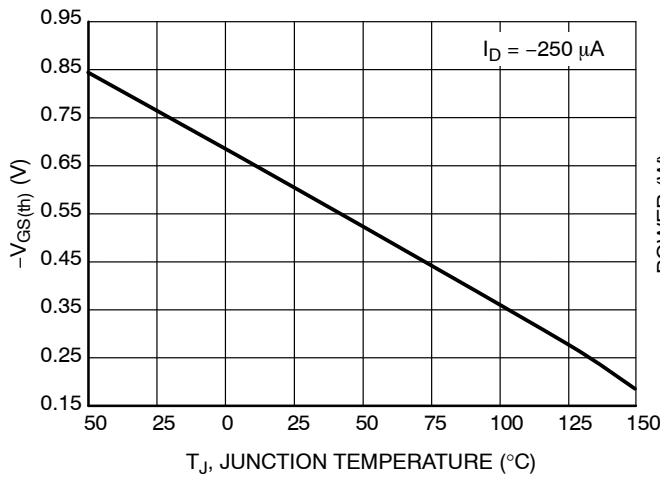


Figure 11. Threshold Voltage

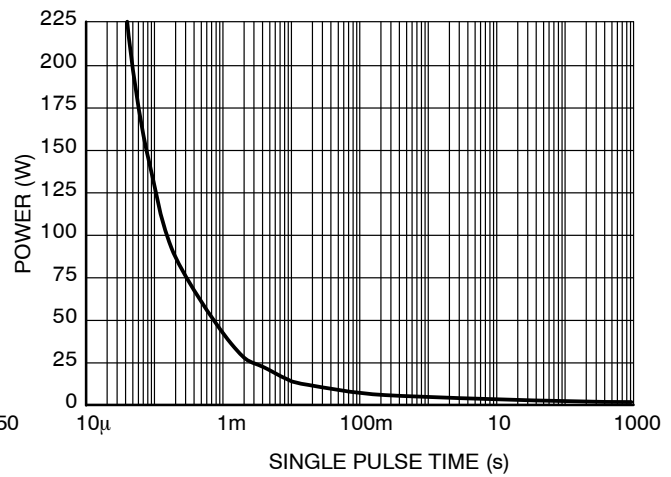


Figure 12. Single Pulse Maximum Power Dissipation

NTLUS3A18PZ

TYPICAL CHARACTERISTICS

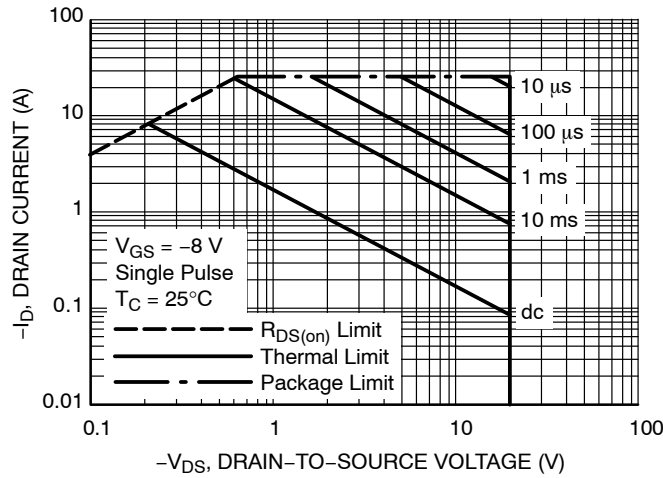


Figure 13. Maximum Rated Forward Biased Safe Operating Area

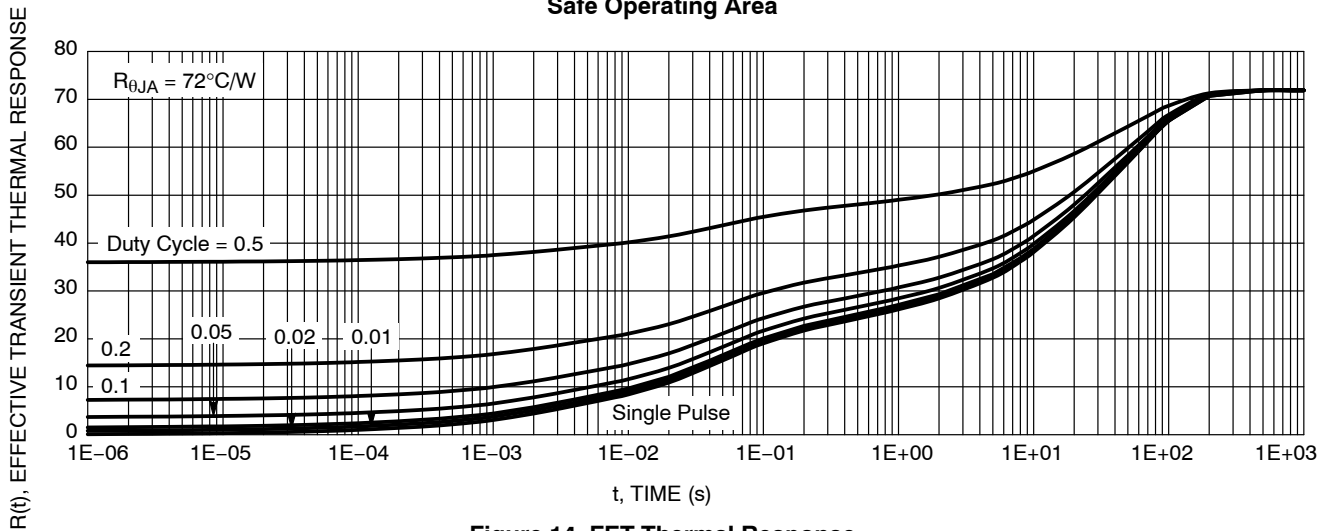


Figure 14. FET Thermal Response

DEVICE ORDERING INFORMATION

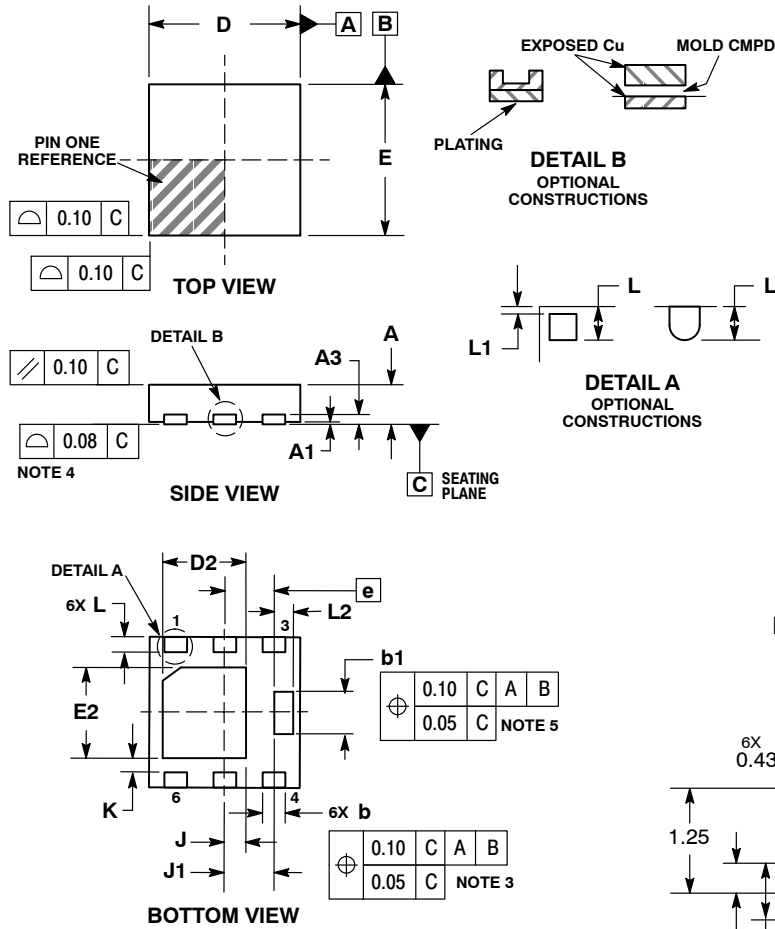
Device	Package	Shipping [†]
NTLUS3A18PZTAG	UDFN6 (Pb-Free)	3000 / Tape & Reel
NTLUS3A18PZTBG	UDFN6 (Pb-Free)	3000 / Tape & Reel
NTLUS3A18PZTCG	UDFN6 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

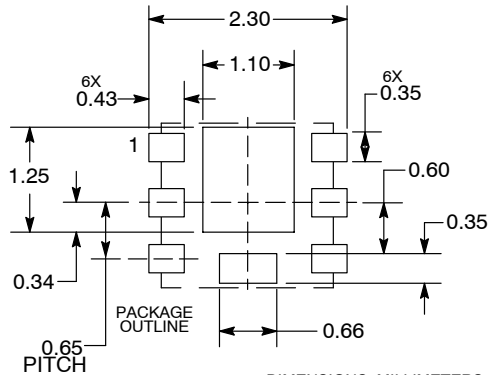
NTLUS3A18PZ

PACKAGE DIMENSIONS

UDFN6 2x2, 0.65P
CASE 517BG
ISSUE A



RECOMMENDED MOUNTING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and the are registered trademarks of Semiconductor Components Industries, LLC (SCILLC) or its subsidiaries in the United States and/or other countries. SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of SCILLC's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marketing.pdf. SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com
Order Literature: <http://www.onsemi.com/orderlit>
For additional information, please contact your local Sales Representative

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

[ON Semiconductor:](#)

[NTLUS3A18PZTBG](#) [NTLUS3A18PZTAG](#) [NTLUS3A18PZTCG](#) [NTLUS3A18PZCTBG](#)